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(54) Title: DINUCLEAR MOLYBDENUM PRECURSORS FOR DEPOSITION OF MOLYBDENUM-CONTAINING FILMS

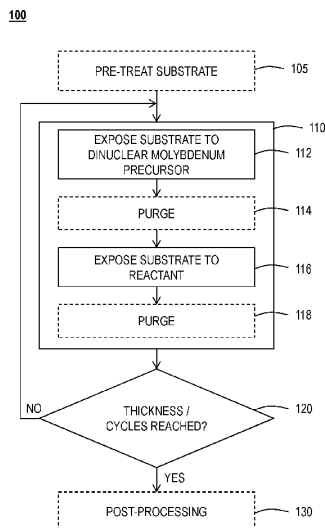


FIG. 1

(57) Abstract: Dinuclear molybdenum coordination complexes are described. Methods for depositing molybdenum-containing films on a substrate are described. The substrate is exposed to a dinuclear molybdenum precursor and a reactant to form the molybdenum-containing film (e.g., elemental molybdenum, molybdenum oxide, molybdenum carbide, molybdenum silicide, molybdenum nitride). The exposures can be sequential or simultaneous.

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